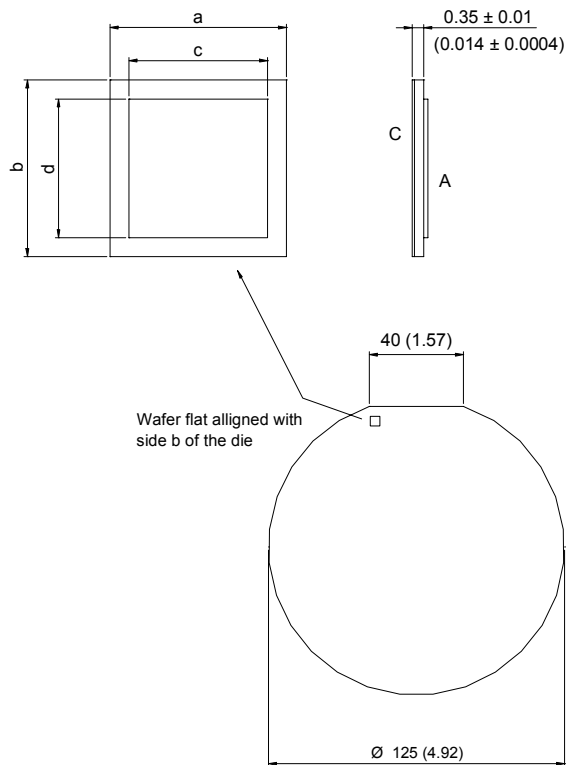


International
IOR Rectifier

FD160H06A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
2. CONTROLLING DIMENSION (INCH):
3. DIMENSIONS AND TOLERANCES:
 $a = 4.064 \pm 0.05$
 (0.160 ± 0.002)
 $b = 4.064 \pm 0.05$
 (0.160 ± 0.002)
 $c = 3.404 \pm 0.003$
 (0.134 ± 0.0001)
 $d = 3.404 \pm 0.003$
 (0.134 ± 0.0001)
4. LETTER DESIGNATION:
A = Anode (Top Metal)
C = Cathode (Back Metal)
5. SAWING:
Recommended Blade
SEMITEC S1025 QS00 Blade
6. MINIMUM ORDER QUANTITY:
500 die

NOT TO SCALE

Reference IR Packaged Part: 30ETH06/ 30EPH06 Series

Electrical Characteristics (Wafer Form)

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	2.3 V	$T_J = 25^\circ\text{C}$, $I_F = 30\text{ A}$
V_{RRM} Minimum Reverse Breakdown Voltage	600 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 200\text{ }\mu\text{A}$
I_{RM} Max. Reverse Leakage Current	100 μA	$T_J = 25^\circ\text{C}$, $V_{RRM} = 600\text{ V}$
t_{rr} Typ. Reverse Recovery Time	20 ns	$I_F = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.160" x 0.160" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code	
	FD 160 H 06 A 5 B ①②③④⑤⑥⑦
1	- Fred Die
2	- Chip Dimension in Mils: 160 = 160x160 square
3	- Process: H = HyperFast
4	- Voltage code Vrrm (*100) eg: 06 = 600V
5	- Chip surface metallization: A = Aluminium (anode), Silver (cathode)
6	- Wafer diameter in inches
7	- Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)